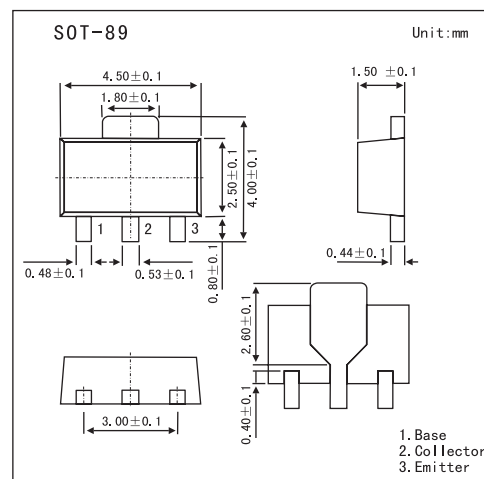


PNP Switching Transistor

PXT2907A

■ Features

- High current (max. 600 mA)
- Low voltage (max. 60 V).

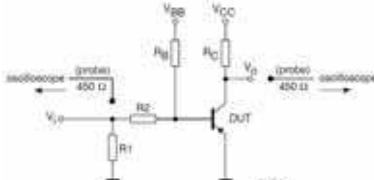


■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-60	V
Collector-emitter voltage	V _{CEO}	-60	V
Emitter-base voltage	V _{EB0}	-5	V
Collector current	I _C	-600	mA
Peak collector current	I _{CM}	-800	mA
Peak base current	I _{BM}	-200	mA
Total power dissipation	P _{tot}	1.3	W
Storage temperature	T _{stg}	-65 to +150	°C
Junction temperature	T _j	150	°C
Operating ambient temperature	R _{amb}	-65 to +150	°C
Thermal resistance from junction to ambient	R _{th(j-a)}	97	K/W
Thermal resistance from junction to soldering point	R _{th(j-s)}	17	K/W

PXT2907A

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	ICBO	IE = 0; VCB = -50 V			-10	nA
		IE = 0; VCB = -50 V; Tj = 125 °C			-10	μA
Emitter cutoff current	IEBO	IC = 0; VEB = -5 V			-50	nA
DC current gain	hFE	IC = -0.1 mA; VCE = -1 V	75			
		IC = -1 mA; VCE = -1 V	100			
		IC = -10 mA; VCE = -1 V	100			
		VCE = -2 V, IC = -150 mA	100		300	
		IC = -500 mA; VCE = -2 V	50			
collector-emitter saturation voltage	VCEsat	IC = -150 mA; IB = -15 mA			-400	mV
		IC = -500 mA; IB = -50 mA			-1.6	V
base-emitter saturation voltage	VBEsat	IC = -150 mA; IB = -15 mA			-1.3	V
		IC = -500 mA; IB = -50 mA			-2.6	V
Collector capacitance	Cc	IE = iE = 0; VCB = -10 V; f = 1 MHz			8	pF
Emitter capacitance	Ce	IC = iC = 0; VEB = -500 mV; f = 1 MHz			35	pF
Transition frequency	fr	IC = -20 mA; VCE = -10 V; f = 100 MHz	200			MHz
Turn-on time	ton	ICon = -150 mA; IBon = -15 mA; IBoff = 15 mA			40	ns
Delay time	td				12	ns
Rise time	tr				30	ns
Turn-off time	toff				365	ns
Storage time	ts				300	ns
Fall time	tf				65	ns

■ Marking

Marking	p2F
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